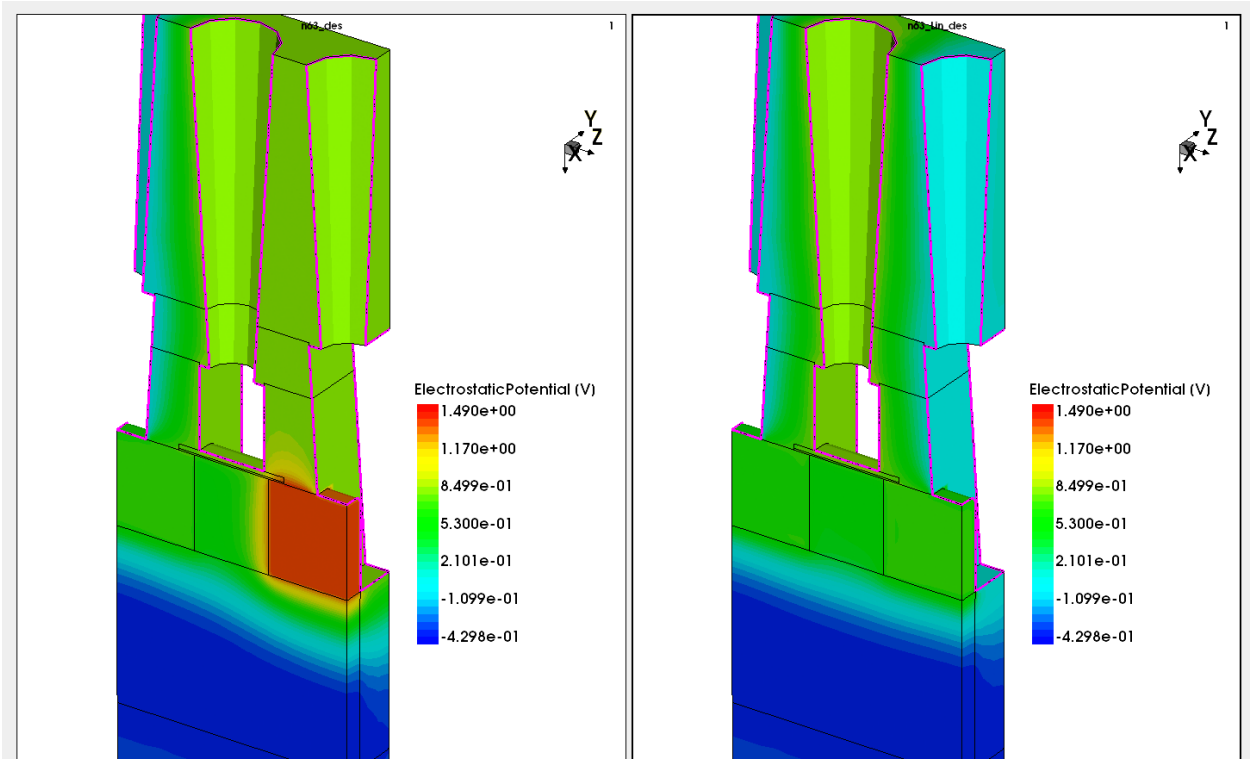


“K. Mehta and H. -Y. Wong, "Prediction of FinFET Current-Voltage and Capacitance-Voltage Curves Using Machine Learning With Autoencoder," in IEEE Electron Device Letters, vol. 42, no. 2, pp. 136-139, Feb. 2021, doi: 10.1109/LED.2020.3045064.”

The following is a snapshot of the structure at different bias conditions for this device

Type	sOri	cDir	Nch	Nstop	L	H	Wbottom	Wtop			Vdd	Strain_Impact	lin	Isat	WF
[n3]: nMOS	[n5]: 100	[n7]: 110	[n9]: 2.0e18	[n11]: 2e18	[n13]: 0.025	[n15]: 0.035	[n17]: 0.015	[n21]: 0.015	[n27]: --	[n33]: --	[n39]: 0.8	[n45]: 1	[n51]: 1	[n57]: 1	[n63]: 4.623

ElectrostaticPotential (Left: $V_G = V_D = 0.8V$, right $V_G = 0.8V$, $V_D=0.05V$)



The data file can be found at

https://drive.google.com/drive/folders/1DkHmNYVe2iX12JI7ATPAySEmUHAJ_4Mz?usp=drive_link